

TECHNICAL DATA
DATA SHEET 4965, REV. -**HERMETIC POWER MOSFET
N-CHANNEL QUAD**

FEATURES:

- 100 Volt, 0.18 Ohm, 5A MOSFET
- Fast Switching
- Low $R_{DS(on)}$
- Characterized at V_{GS} of 6V

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
ON-STATE DRAIN CURRENT	I_D	-	-	5	Amps
PULSED DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	I_{DM}	-	-	20	Amps
OPERATING AND STORAGE TEMPERATURE	T_J/T_{STG}	-55	-	+150	$^\circ\text{C}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	P_D	-	-	27	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	4.7	$^\circ\text{C/W}$

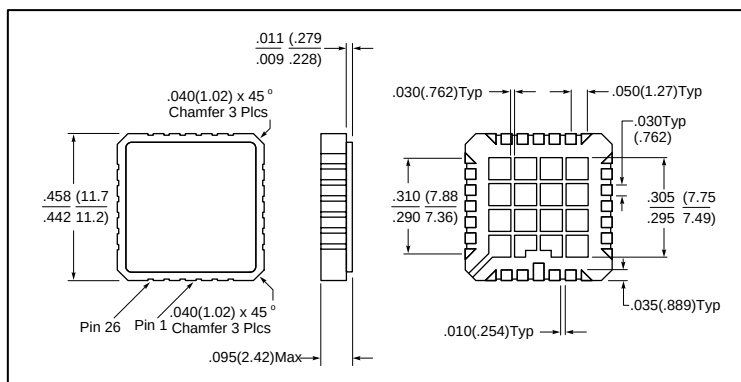
ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	100	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}, I_D = 3.6\text{A}$	$R_{DS(ON)}$	-	-	0.18	Ω
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 6\text{V}, I_D = 2.4\text{A}$	$R_{DS(ON)}$	-	-	0.20	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} = 15\text{V}; I_{DS} = 3.6\text{A}$	g_{fs}	-	7	-	$\text{S}(1/\Omega)$
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 0.8 \times \text{Max. rating}, V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$	I_{DSS}	-	-	1 100	μA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20\text{V}$	I_{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20\text{V}$				-100	
TURN ON DELAY TIME $V_{DD} = 50\text{V},$	$t_{d(ON)}$	-	-	30	nsec
RISE TIME $I_D = 3.6\text{A},$	t_r			30	
TURN OFF DELAY TIME $R_G = 6\Omega$	$t_{d(OFF)}$			40	
FALL TIME	t_f			30	
DIODE FORWARD VOLTAGE $I_S = 7.4\text{A}, V_{GS} = 0\text{V}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$	V_{SD}	-	-	1.5	Volts
REVERSE RECOVERY TIME $T_J = 25^\circ\text{C}$ $I_f = 3.6\text{A}$ $di/dt \leq 100\text{A}/\mu\text{sec}$	t_{rr}	-	-	80	nsec
INPUT CAPACITANCE $V_{GS} = 0\text{V}$	C_{iss}	-	370	-	pF
OUTPUT CAPACITANCE $V_{DS} = 25\text{V}$	C_{oss}		60		
REVERSE TRANSFER CAPACITANCE $f = 1.0\text{MHz}$	C_{rss}		30		

SENSITRON

DATA SHEET 4965, REV. -

MECHANICAL DIMENSIONS: in Inches / m

**LCC-28T****PINOUT TABLE**

QUAD MOSFET LCC-28T	GATE	DRAIN	SOURCE
MOSFET 1	PIN 1	PINS 5, 6, 7	PINS 2, 3, 4
MOSFET 2	PIN 8	PINS 9, 10, 11	PINS 12, 13, 14
MOSFET 3	PIN 15	PINS 19, 20, 21	PINS 16, 17, 18
MOSFET 4	PIN 22	PINS 23, 24, 25	PINS 26, 27, 28

DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.